

Intelligent Power Module (IPM), 650 V, 50 A



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NFAM5065L4BT

General Description

The NFAM5065L4BT is a fully-integrated inverter power module consisting of an independent High side gate driver, LVIC, six IGBT's and a temperature sensor (VTS or Thermistor (T)), suitable for driving permanent magnet synchronous (PMSM) motors, brushless DC (BLDC) motors and AC asynchronous motors. The IGBT's are configured in a three-phase bridge with separate emitter connections for the lower legs for maximum flexibility in the choice of control algorithm.

The power stage has under voltage lockout protection (UVP). Internal boost diodes are provided for high side gate boost drive.

Features

- Three-phase 650 V, 50 A IGBT Module with Independent Drivers
- Active Logic Interface
- Built-in Undervoltage Protection (UVP)
- Integrated Bootstrap Diodes and Resistors
- Separate Low-side IGBT Emitter Connections for Individual Current Sensing of Each Phase
- Temperature Sensor (VTS or Thermistor (T))
- UL1557 Certified (File No.339285)
- This Device is Pb-Free and RoHS Compliant

Typical Applications

- Industrial Drives
- Industrial Pumps
- Industrial Fans
- Industrial Automation

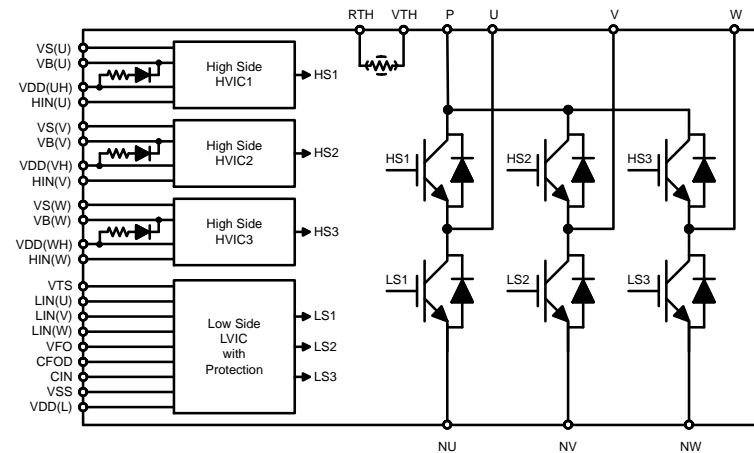
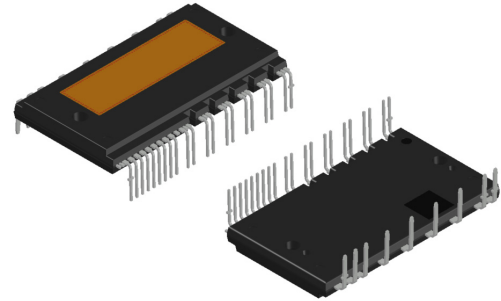


Figure 1. Application Schematic



DIP39 54.5 x 31.0
CASE MODGC

MARKING DIAGRAM



Device marking is on package top side

NFAM5065L4BT = Specific Device Code
ZZZ = Assembly Lot Code
A = Assembly Location
T = Test Location
Y = Year
WW = Work Week

ORDERING INFORMATION

| Device | Package | Shipping |
|--------------|-----------------------------------|----------|
| NFAM5065L4BT | DIP39 54.5 x 31.0 (Pb-Free) | 90 / Box |

NFAM5065L4BT

APPLICATION SCHEMATIC

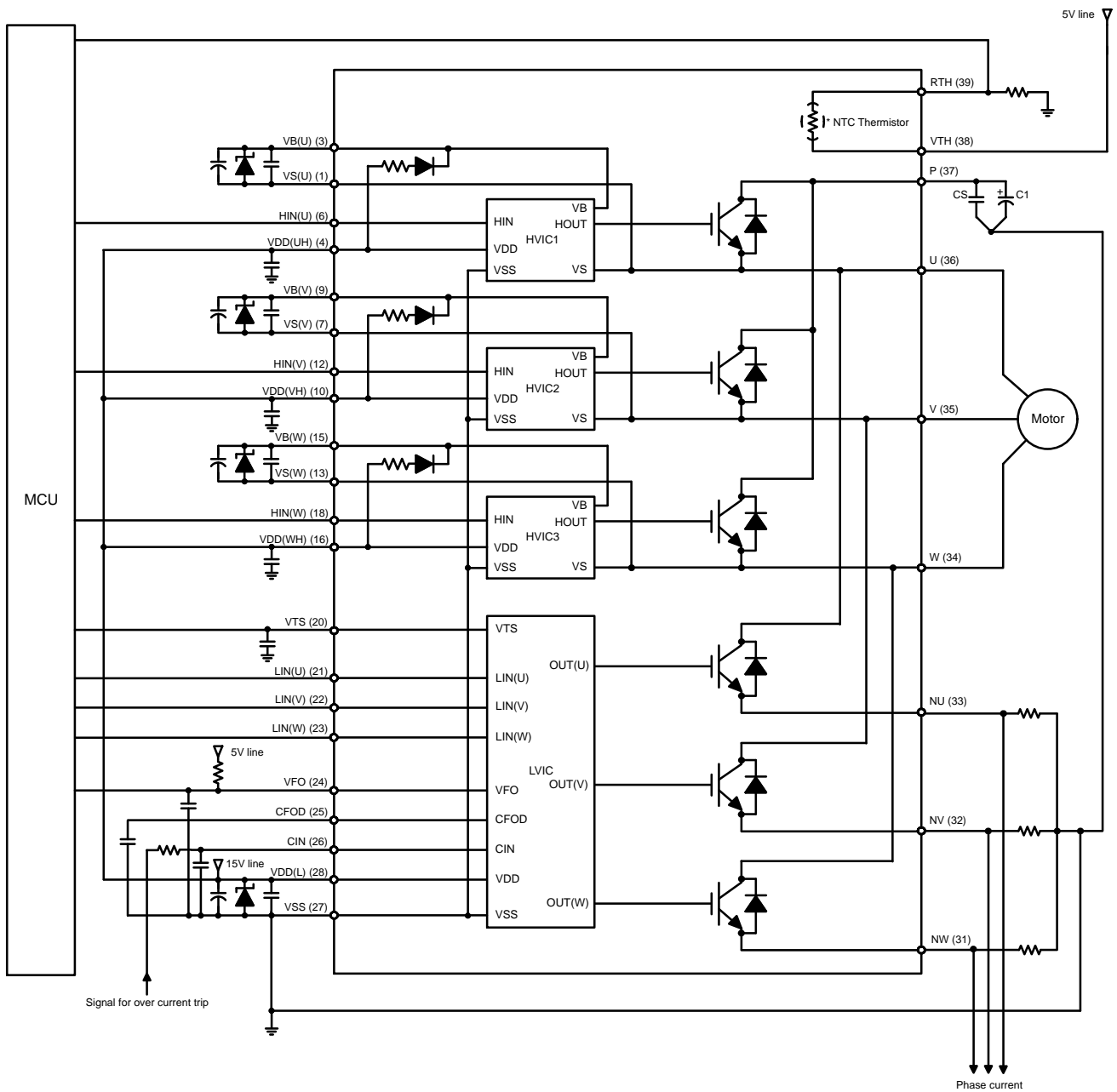


Figure 2. Application Schematic – Adjustable Option

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BLOCK DIAGRAM

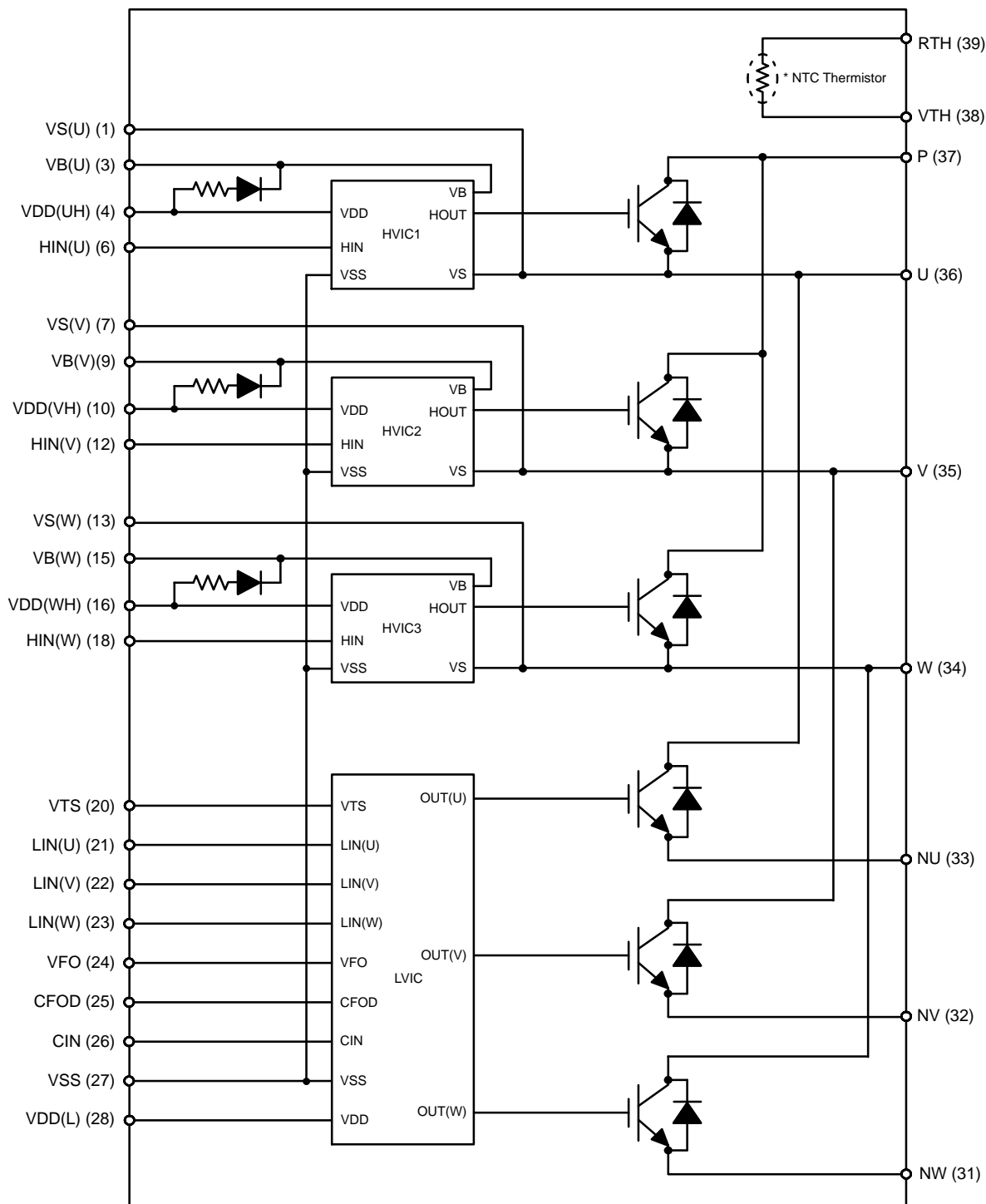


Figure 3. Equivalent Block Diagram

NFAM5065L4BT

PIN FUNCTION DESCRIPTION

| Pin | Name | Description |
|------|---------|--|
| 1 | VS(U) | High-Side Bias Voltage GND for U phase IGBT Driving |
| (2) | - | Dummy |
| 3 | VB(U) | High-Side Bias Voltage for U phase IGBT Driving |
| 4 | VDD(UH) | High-Side Bias Voltage for U phase IC |
| (5) | - | Dummy |
| 6 | HIN(U) | Signal Input for High-Side U Phase |
| 7 | VS(V) | High-Side Bias Voltage GND for V phase IGBT Driving |
| (8) | - | Dummy |
| 9 | VB(V) | High-Side Bias Voltage for V phase IGBT Driving |
| 10 | VDD(VH) | High-Side Bias Voltage for V phase IC |
| (11) | - | Dummy |
| 12 | HIN(V) | Signal Input for High-Side V Phase |
| 13 | VS(W) | High-Side Bias Voltage GND for W phase IGBT Driving |
| (14) | - | Dummy |
| 15 | VB(W) | High-Side Bias Voltage for W phase IGBT Driving |
| 16 | VDD(WH) | High-Side Bias Voltage for W phase IC |
| (17) | - | Dummy |
| 18 | HIN(W) | Signal Input for High-Side W Phase |
| (19) | - | Dummy |
| 20 | VTS | Voltage Output for LVIC Temperature Sensing Unit |
| 21 | LIN(U) | Signal Input for Low-Side U Phase |
| 22 | LIN(V) | Signal Input for Low-Side V Phase |
| 23 | LIN(W) | Signal Input for Low-Side W Phase |
| 24 | VFO | Fault Output |
| 25 | CFOD | Capacitor for Fault Output Duration Selection |
| 26 | CIN | Input for Current Protection |
| 27 | VSS | Low-Side Common Supply Ground |
| 28 | VDD(L) | Low-Side Bias Voltage for IC and IGBTs Driving |
| (29) | - | Dummy |
| (30) | - | Dummy |
| 31 | NW | Negative DC-Link Input for U Phase |
| 32 | NV | Negative DC-Link Input for V Phase |
| 33 | NU | Negative DC-Link Input for W Phase |
| 34 | W | Output for U Phase |
| 35 | V | Output for V Phase |
| 36 | U | Output for W Phase |
| 37 | P | Positive DC-Link Input |
| 38 | VTH | Thermistor Bias Voltage (T) / Not connection |
| 39 | RTH | Series Resistor for Thermistor (Temperature Detection) *optional for T |

1. Pins of () are the dummy for internal connection. These pins should be no connection.

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ABSOLUTE MAXIMUM RATINGS (T_C = 25°C) (Note 2)

| Symbol | Rating | Conditions | Value | Unit |
|------------------|--|---|-------------|------|
| VPN | Supply Voltage | P–NU, NV, NW | 450 | V |
| VPN(surge) | Supply Voltage (Surge) | P–NU, NV, NW (Note 3) | 550 | V |
| VPN(PROT) | Self Protection Supply Voltage Limit (Short–Circuit Protection Capability) | VDD = VBS = 13.5 V ~ 16.5 V, T _J = 150°C, VCES < 650 V, Non–Repetitive, < 2 μs | 400 | V |
| Vces | Collector–emitter voltage | | 650 | V |
| VRRM | Maximum Repetitive Revers Voltage | | 650 | V |
| ±Ic | Each IGBT Collector Current | | ±30 | A |
| Iop | Output current (peak) | PWM control | ±50 | A |
| ±Icp | Each IGBT Collector Current (Peak) | Under 1 ms Pulse Width | ±100 | A |
| VDD | Control Supply Voltage | VDD(UH,VH,WH), VDD(L)–VSS | –0.3 to 20 | V |
| VBS | High–Side Control Bias voltage | VB(U)–VS(U), VB(V)–VS(V), VB(W)–VS(W) | –0.3 to 20 | V |
| VIN | Input Signal Voltage | HIN(U), HIN(V), HIN(W), LIN(U), LIN(V), LIN(W)–VSS | –0.3 to VDD | V |
| VFO | Fault Output Supply Voltage | VFO–VSS | –0.3 to VDD | V |
| IFO | Fault Output Current | Sink Current at VFO pin | 2 | mA |
| VCIN | Current Sensing Input Voltage | CIN–VSS | –0.3 to VDD | V |
| Pc | Corrector Dissipation | Per One Chip | 125 | W |
| T _J | Operating Junction Temperature | | –40 to +150 | °C |
| T _{stg} | Storage temperature | | –40 to +125 | °C |
| T _c | Module Case Operation Temperature | | –40 to +125 | °C |
| V _{ISO} | Isolation voltage | 60 Hz, Sinusoidal, AC 1 minute, Connection Pins to Heat Sink Plate | 2500 | Vrms |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Refer to [ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES](#) and/or APPLICATION INFORMATION for Safe Operating parameters.
- This surge voltage developed by the switching operation due to the wiring inductance between P and NU, NV, NW terminal.

THERMAL CHARACTERISTICS

| Symbol | Rating | Conditions | Min | Typ | Max | Unit |
|-----------------------|-------------------------------------|-------------------------------------|-----|-----|-----|------|
| R _{th(j-c)Q} | Junction-to-Case Thermal Resistance | Inverter IGBT Part (per 1/6 module) | – | – | 1.0 | °C/W |
| R _{th(j-c)F} | | Inverter FWD Part (per 1/6 module) | – | – | 1.7 | °C/W |

- Refer to [ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES](#) and/or APPLICATION INFORMATION for Safe Operating parameters.

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RECOMMENDED OPERATING CONDITIONS (Note 5)

| Symbol | Rating | Conditions | Min | Typ | Max | Unit | |
|----------------------|-----------------------------|---|---------------|-----|------|------------|------|
| VPN | Supply Voltage | P-NU, NV, NW | - | 300 | 400 | V | |
| VDD | Gate Driver Supply Voltages | VDD(UH,VH,WH), VDD(L)-VSS | 13.5 | 15 | 16.5 | V | |
| VBS | | VB(U)-VS(U), VB(V)-VS(V), VB(W)-VS(W) | 13.0 | 15 | 18.5 | V | |
| dVDD / dt, dVBS / dt | Supply Voltage Variation | | -1 | - | 1 | V/ μ s | |
| fPWM | PWM Frequency | | 1 | - | 20 | kHz | |
| DT | Dead Time | Turn-off to Turn-on (external) | 1.5 | - | - | μ s | |
| Io | Allowable r.m.s. Current | VPN = 300 V, VDD = 15 V, P.F. = 0.8, Tc \leq 125°C, Tj \leq 150°C (Note 5) | fPWM = 5 kHz | - | - | 30.0 | Arms |
| | | | fPWM = 15 kHz | - | - | 21.2 | |
| PWIN (on) | Allowable Input Pulse Width | 200 V \leq VPN \leq 400 V 13.5 V \leq VDD \leq 16.5 V 13.0 V \leq VBS \leq 18.5 V -20°C \leq Tc \leq 100°C | 1.0 | - | - | μ s | |
| PWIN (off) | | | 1.5 | - | - | | |
| | Package Mounting Torque | M3 type screw | 0.6 | 0.7 | 0.9 | Nm | |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Allowable r.m.s current depends on the actual conditions.

6. Flatness tolerance of the heatsink should be within -50 μ m to +100 μ m.

ELECTRICAL CHARACTERISTICS (T_C = 25°C, VDD = 15 V, VBS = 15 V, unless otherwise specified.) (Note 7)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|--------|-----------|-----------------|-----|-----|-----|------|
|--------|-----------|-----------------|-----|-----|-----|------|

INVERTERSECTION

| | | | | | | | | |
|----------|--------------------------------------|-----------|---|---|------|------|---------|---------|
| Ices | Collector-Emitter Leakage Current | | Vce = Vces, T _J = 25°C | - | - | 1 | mA | |
| | | | Vce = Vces, T _J = 150°C | - | - | 10 | mA | |
| VCE(sat) | Collector-Emitter Saturation Voltage | | VDD = VBS = 15 V, IN = 5 V Ic = 50 A, T _J = 25°C | - | 1.65 | 2.30 | V | |
| | | | VDD = VBS = 15 V, IN = 5 V Ic = 50 A, T _J = 150°C | - | 1.85 | - | V | |
| VF | FWDi Forward Voltage | | IN = 0 V, Ic = 50 A, T _J = 25°C | - | 2.00 | 2.40 | V | |
| | | | IN = 0 V, Ic = 50 A, T _J = 150°C | - | 2.00 | - | V | |
| ton | Switching Times | High Side | VPN = 300 V, VDD(H) = VDD(L) = 15 V Ic = 50 A, T _J = 25°C, IN = 0 \leftrightarrow 5 V Inductive Load | 0.90 | 1.50 | 2.10 | μ s | |
| tc(on) | | | | - | 0.40 | 0.70 | μ s | |
| toff | | | | - | 1.80 | 2.40 | μ s | |
| tc(off) | | | | - | 0.25 | 0.75 | μ s | |
| trr | | | | - | 0.25 | - | μ s | |
| ton | | Low Side | | VPN = 300 V, VDD(H) = VDD(L) = 15 V Ic = 50 A, T _J = 25°C, IN = 0 \leftrightarrow 5 V Inductive Load | 0.90 | 1.50 | 2.10 | μ s |
| tc(on) | | | | | - | 0.30 | 0.60 | μ s |
| toff | | | | | - | 1.70 | 2.30 | μ s |
| tc(off) | | | | | - | 0.25 | 0.75 | μ s |
| trr | | | | | - | 0.25 | - | μ s |

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, $V_{DD} = 15\text{ V}$, $V_{BS} = 15\text{ V}$, unless otherwise specified.) (Note 7) (continued)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|-----------------------|--|--|-------|-------|-------|------|
| DRIVER SECTION | | | | | | |
| IQDDH | Quiescent VDD Supply Current | $V_{DD}(UH, VH, WH) = 15\text{ V}$, $HIN(U, V, W) = 0\text{ V}$ | | | 0.30 | mA |
| IQDDL | | $V_{DD}(L) = 15\text{ V}$, $LIN(U, V, W) = 0\text{ V}$ | | | 3.50 | mA |
| IPDDH | Operating VCC Supply Current | $V_{DD}(UH, VH, WH) = 15\text{ V}$, $f_{PWM} = 20\text{ kHz}$, Duty = 50%, Applied to one PWM Signal Input for High-Side | | | 0.40 | mA |
| IPDDL | | $V_{DD}(L) = 15\text{ V}$, $f_{PWM} = 20\text{ kHz}$, Duty = 50%, Applied to one PWM Signal Input for Low-Side | | | 6.00 | mA |
| IQBS | Quiescent VBS Supply Current | $V_{BS} = 15\text{ V}$, $HIN(U, V, W) = 0\text{ V}$ | | | 0.30 | mA |
| IPBS | Operating VBS Supply Current | $V_{DD} = V_{BS} = 15\text{ V}$, $f_{PWM} = 20\text{ kHz}$, Duty = 50%, Applied to one PWM Signal Input for High-Side | | | 5.00 | mA |
| VIN(ON) | ON Threshold Voltage | $HIN(U, V, W) - V_{SS}$, $LIN(U, V, W) - V_{SS}$ | | | 2.6 | V |
| VIN(OFF) | OFF Threshold Voltage | | 0.8 | | | V |
| VCIN(ref) | Short Circuit Trip Level | $V_{DD} = 15\text{ V}$, $CIN - V_{SS}$ | 0.46 | 0.48 | 0.50 | V |
| UVDDD | Supply Circuit Under-Voltage Protection | Detection Level | 10.3 | | 12.5 | V |
| UVDDR | | Reset Level | 10.8 | | 13.0 | V |
| UVBSD | | Detection Level | 10.0 | | 12.0 | V |
| UVBSR | | Reset Level | 10.5 | | 12.5 | V |
| VTS | Voltage Output for LVIC Temperature Sensing Unit | $V_{TS} - V_{SS} = 10\text{ nF}$, Temp. = 25°C | 0.905 | 1.030 | 1.155 | V |
| VFOH | Fault Output Voltage | $V_{DD} = 0\text{ V}$, $CIN = 0\text{ V}$, VFO Circuit: $10\text{ k}\Omega$ to 5 V Pull-up | 4.9 | | | V |
| VFOL | | $V_{DD} = 0\text{ V}$, $CIN = 1\text{ V}$, VFO Circuit: $10\text{ k}\Omega$ to 5 V Pull-up | | | 0.95 | V |
| t_{FOD} | Fault-Output Pulse Width | $CFOD = 22\text{ nF}$ | 1.6 | 2.4 | | ms |

BOOTSTRAP SECTION

| | | | | | | |
|-------|---------------------------------|----------------------|-----|-----|-----|----------|
| VF | Bootstrap Diode Forward Voltage | $I_f = 0.1\text{ A}$ | 3.4 | 4.6 | 5.8 | V |
| RBOOT | Built-in Limiting Resistance | | 30 | 38 | 46 | Ω |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Performance guaranteed over the indicated operating temperature range by design and/or characterization tested at $T_J = T_A = 25^\circ\text{C}$.

Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

8. The fault-out pulse width t_{FOD} depends on the capacitance value of CFOD according to the following approximate equation:

$$t_{FOD} = 0.1 \times 10^6 \times CFOD \text{ (s)}$$

9. Values based on design and/or characterization.

NFAM5065L4BT

Temperature of LVIC versus VTS Characteristics

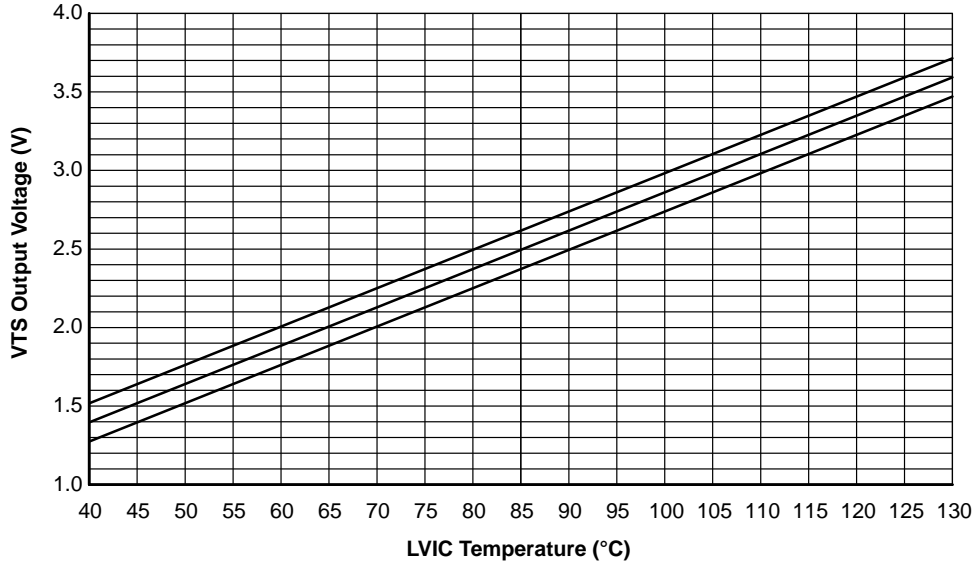


Figure 4. Temperature of LVIC versus VTS Characteristics

Table 1. THERMISTOR CHARACTERISTICS (INCLUDED ONLY IN NFAM5060L4BT)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|----------------------|-----------|---------------------------|--------|-------|--------|------------------|
| Resistance | R_{25} | $T_c = 25^\circ\text{C}$ | 46.530 | 47 | 47.47 | $\text{k}\Omega$ |
| Resistance | R_{125} | $T_c = 100^\circ\text{C}$ | 1.344 | 1.406 | 1.471 | $\text{k}\Omega$ |
| B-Constant (25–50°C) | – | B | 4009.5 | 4050 | 4090.5 | K |
| Temperature range | – | – | –40 | – | +125 | $^\circ\text{C}$ |

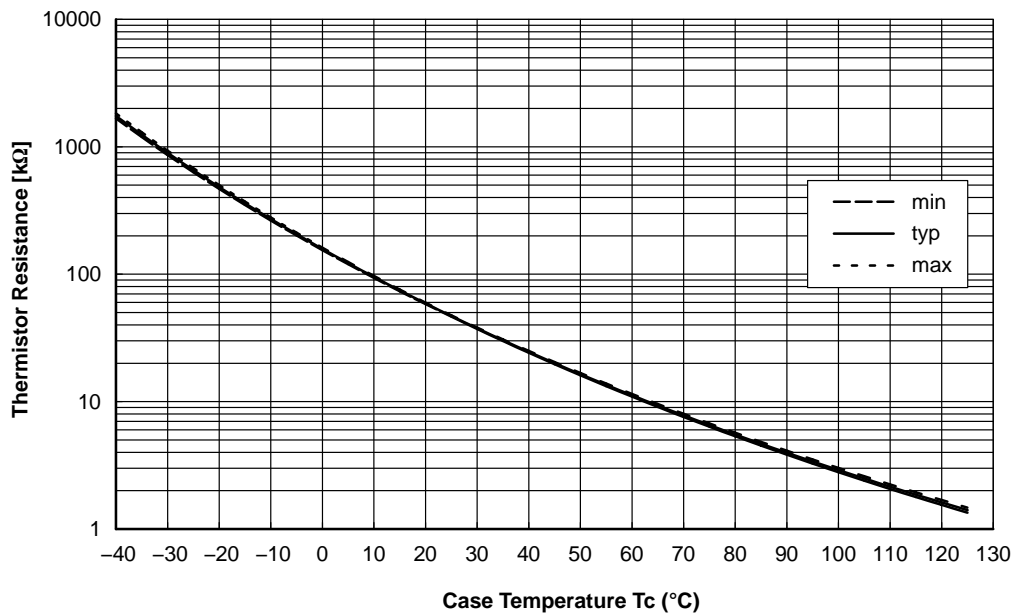
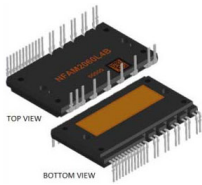


Figure 5. Thermistor Resistance versus Case Temperature

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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MINI DIP39, 31.0x54.5 CASE MODGC ISSUE A

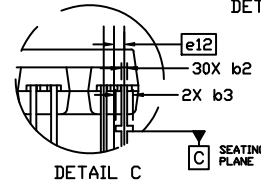
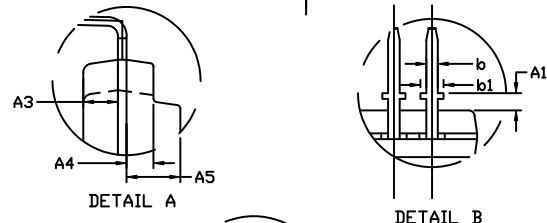
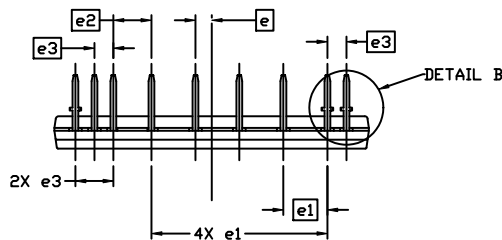
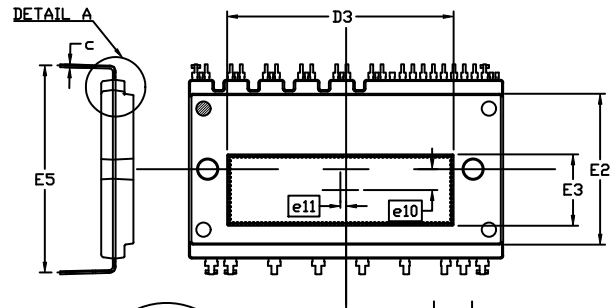
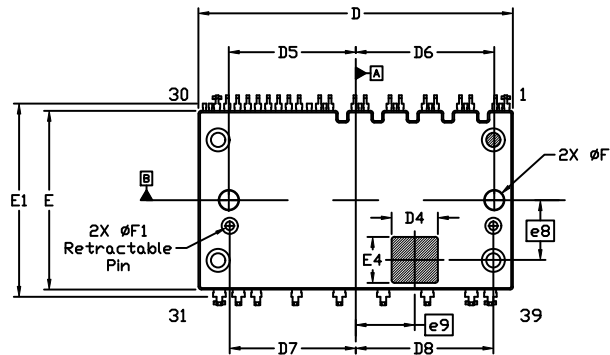
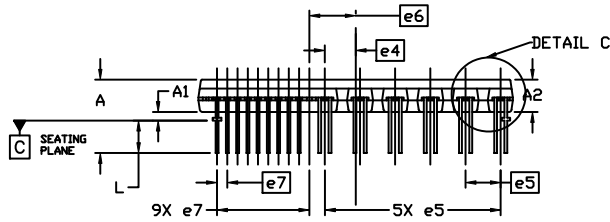
DATE 19 MAR 2019

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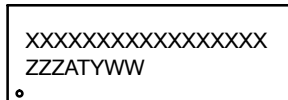
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION *b* and *c* APPLY TO THE PLATED LEADS AND ARE MEASURED BETWEEN 1.00 AND 2.00 FROM THE LEAD TIP.
4. POSITION OF THE LEAD IS DETERMINED AT THE ROOT OF THE LEAD WHERE IT EXITS THE PACKAGE BODY.
5. SHORTENED/CUT PINS ARE 2,5,8,11,14,17,19,29 AND 30.

| MILLIMETERS | | | |
|-------------|-----------|-------|-------|
| DIM | MIN. | NOM. | MAX. |
| A | 12.20 | 12.7 | 13.2 |
| A1 | 1.00 | 1.50 | 2.00 |
| A2 | 5.50 | 5.60 | 5.70 |
| A3 | 2.00 REF | | |
| A4 | 1.55 REF | | |
| A5 | 3.10 REF | | |
| b | 0.90 | 1.00 | 1.10 |
| b1 | 1.90 | 2.00 | 2.10 |
| b2 | 0.40 | 0.50 | 0.60 |
| b3 | 1.40 | 1.50 | 1.60 |
| c | 0.50 REF | | |
| D | 54.40 | 54.50 | 54.60 |
| D3 | 39.25 REF | | |
| D4 | 8.00 REF | | |
| D5 | 22.00 REF | | |
| D6 | 24.00 REF | | |
| D7 | 21.85 REF | | |
| D8 | 23.85 REF | | |

| MILLIMETERS | | | |
|-------------|-----------|-------|-------|
| DIM | MIN. | NOM. | MAX. |
| E | 30.90 | 31.00 | 31.10 |
| E1 | 33.50 REF | | |
| E2 | 26.14 REF | | |
| E3 | 12.35 REF | | |
| E4 | 8.00 REF | | |
| E5 | 35.40 | 35.90 | 36.40 |
| e | 2.81 REF | | |
| e1 | 7.62 BSC | | |
| e2 | 6.60 BSC | | |
| e3 | 3.30 BSC | | |
| e4 | 5.35 REF | | |
| e5 | 6.10 BSC | | |
| e6 | 8.02 REF | | |
| e7 | 1.78 BSC | | |
| e8 | 10.35 REF | | |
| e9 | 10.25 REF | | |
| e10 | 3.60 REF | | |
| e11 | 1.00 REF | | |
| e12 | 0.89 BSC | | |
| F | 3.20 | 3.30 | 3.40 |
| F1 | 1.40 | 1.50 | 1.60 |
| L | 5.60 REF | | |



GENERIC MARKING DIAGRAM*



- XXXXX = Specific Device Code
- ZZZ = Assembly Lot Code
- AT = Assembly & Test Location
- Y = Year
- WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

| | | |
|-------------------------|------------------------------|--|
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| DESCRIPTION: | MINI DIP39, 31.0x54.5 | PAGE 1 OF 1 |

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- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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